



STP80N70F6

N-channel 68 V, 0.0063 Ω typ., 96 A STripFET™ VI DeepGATE™ Power MOSFET in TO-220 package

Datasheet – production data

Features

Order code	V _{DSS} max.	R _{DS(on)} max.	I _D	P _{TOT}
STP80N70F6	68 V	< 0.008 Ω (V _{GS} = 10 V)	96 A	110 W

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses
- Very low switching gate charge

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

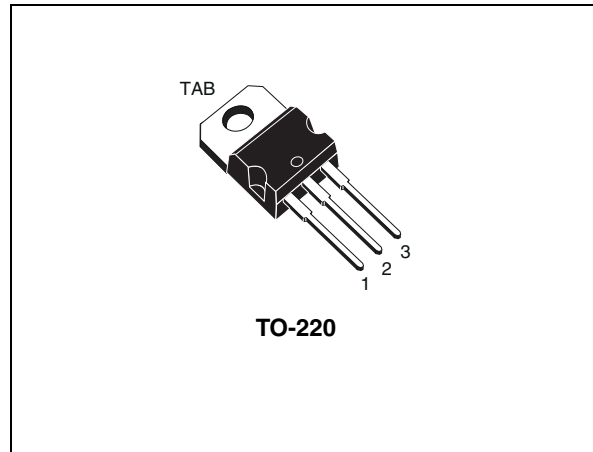


Figure 1. Internal schematic diagram

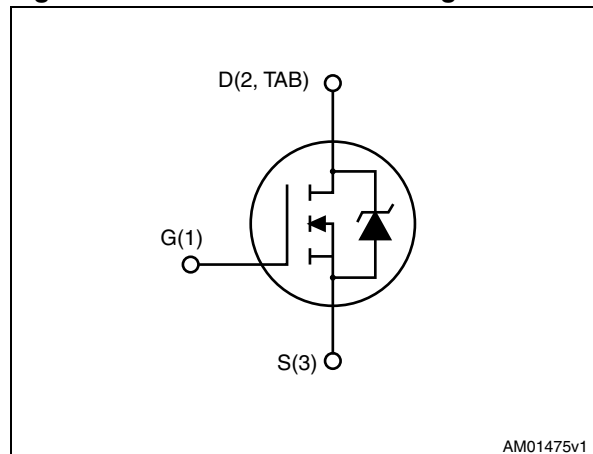


Table 1. Device summary

Order code	Marking	Package	Packaging
STP80N70F6	80N70F6	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Revision history	12

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	68	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	96	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	60	A
$I_{DM}^{(1)}$	Drain current (pulsed)	384	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. This value is rated according to R_{thj-c}

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-c}	Thermal resistance junction-case max	1.36	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu\text{A}$	68			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = 68\ \text{V}$ $V_{DS} = 68\ \text{V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}, I_D = 48\ \text{A}$		0.0063	0.008	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			5850		pF
C_{oss}	Output capacitance	$V_{DS} = 25\ \text{V}, f = 1\ \text{MHz},$ $V_{GS} = 0$	-	341	-	pF
C_{rss}	Reverse transfer capacitance			240		pF
Q_g	Total gate charge	$V_{DD} = 34\ \text{V}, I_D = 96\ \text{A},$ $V_{GS} = 10\ \text{V}$		99		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\ \text{V}$ <i>(see Figure 14)</i>	-	31	-	nC
Q_{gd}	Gate-drain charge			19		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 10\ \text{V}, I_D = 48\ \text{A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\ \text{V}$ <i>(see Figure 13)</i>	-	23	-	ns
t_r	Rise time			29		
$t_{d(off)}$	Turn-off-delay time	<i>(see Figure 13)</i>	-	102	-	ns
t_f	Fall time			23		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		96	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		384	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 96 \text{ A}, V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 48 \text{ A}, V_{DD} = 24 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150 \text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	34		ns
Q_{rr}	Reverse recovery charge			53		nC
I_{RRM}	Reverse recovery current			3		A

1. Pulse width is limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

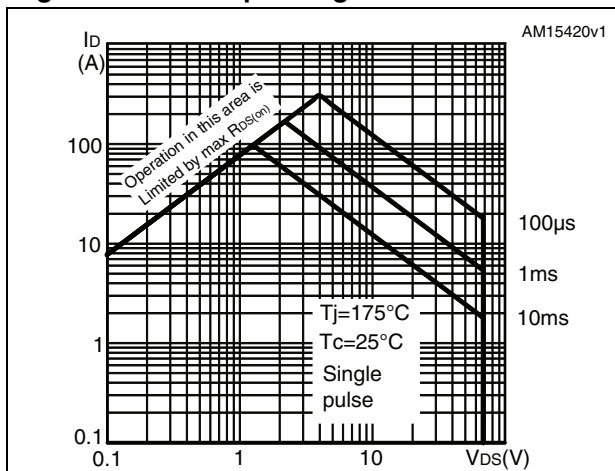


Figure 3. Thermal impedance

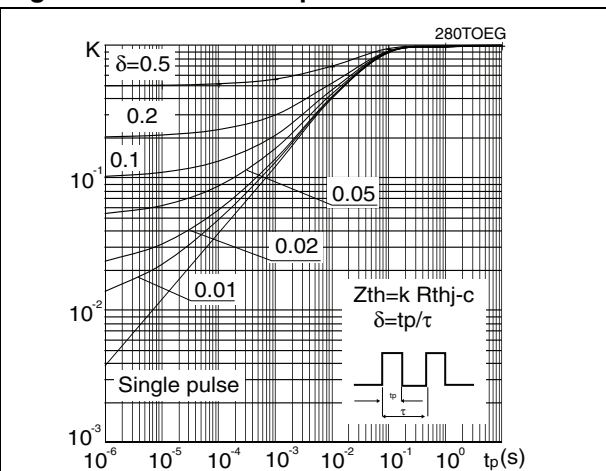


Figure 4. Output characteristics

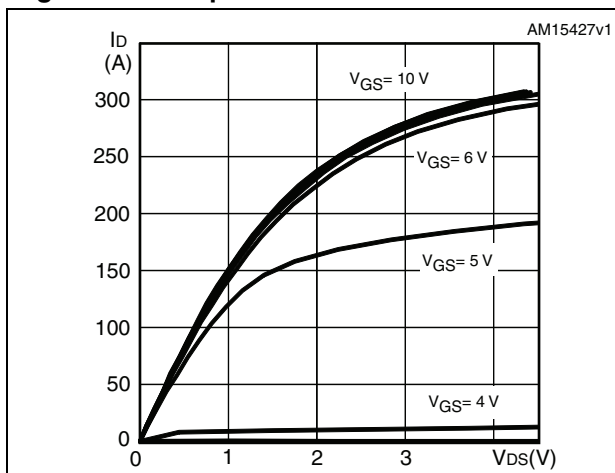


Figure 5. Transfer characteristics

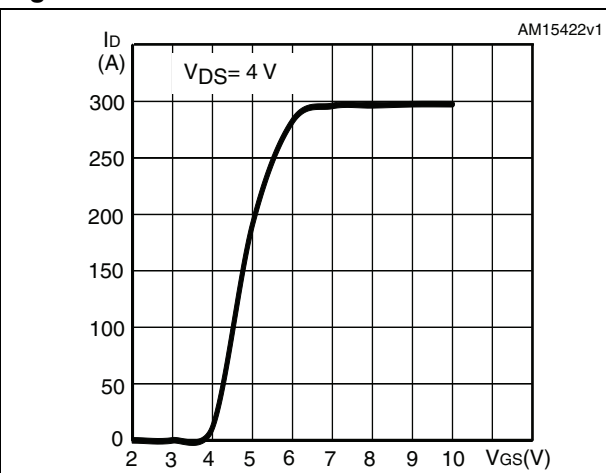


Figure 6. Gate charge vs gate-source voltage

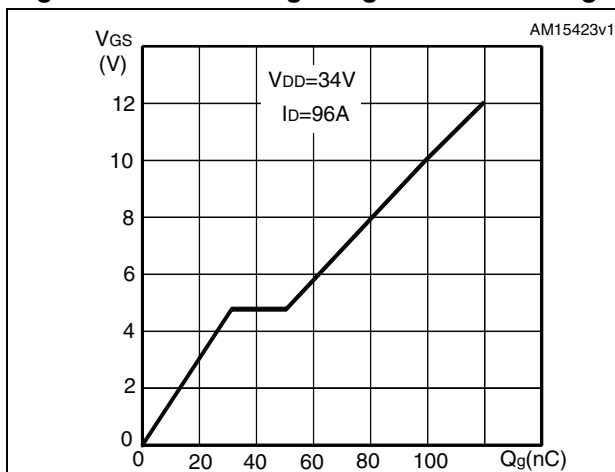


Figure 7. Static drain-source on-resistance

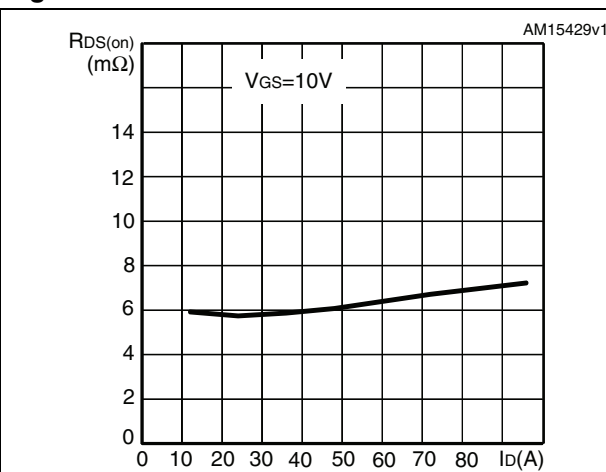


Figure 8. Capacitance variations

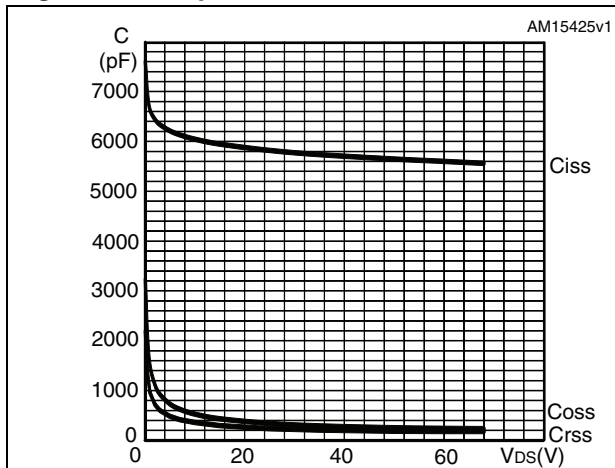


Figure 9. Normalized $B_{V_{DS}}$ vs temperature

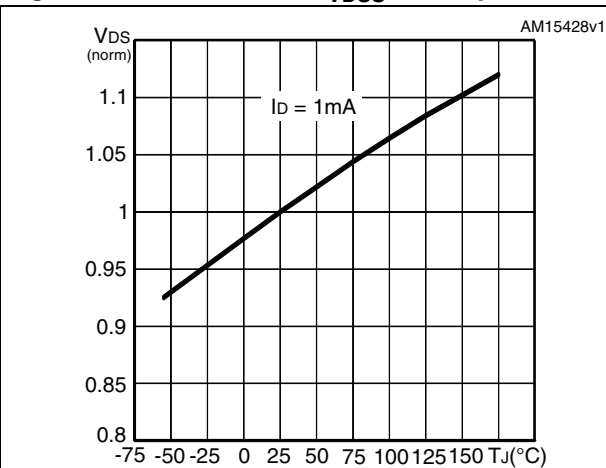


Figure 10. Normalized gate threshold voltage vs temperature

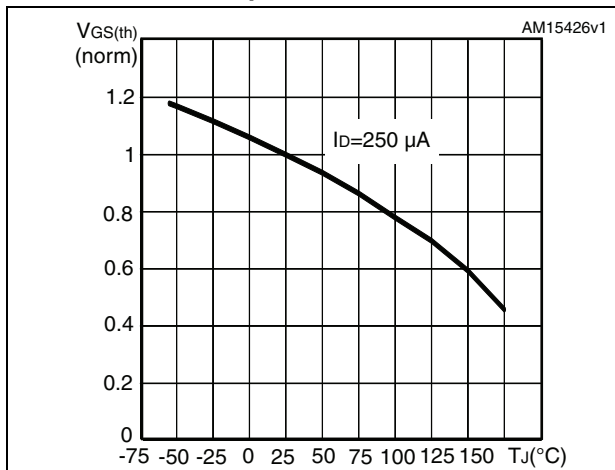


Figure 11. Normalized on-resistance vs temperature

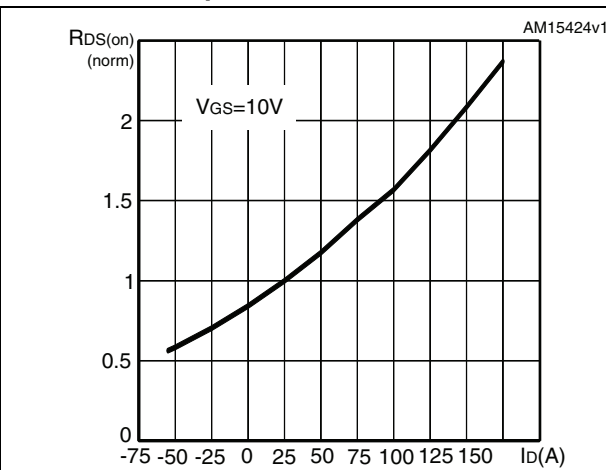
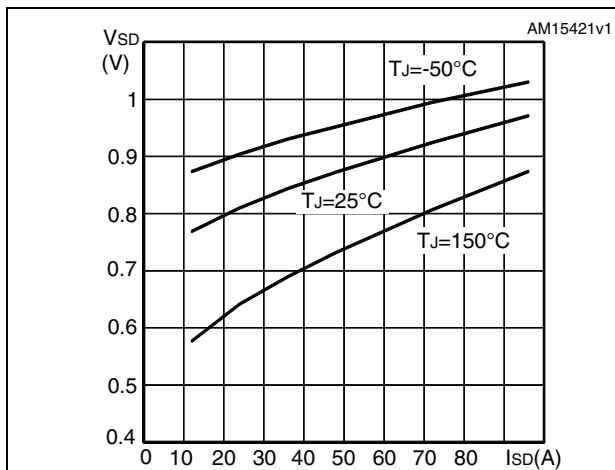
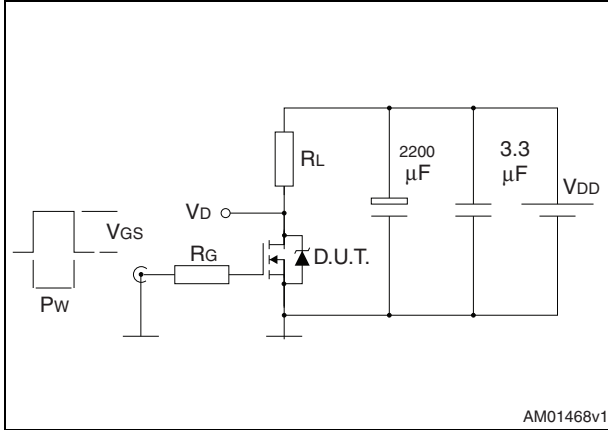


Figure 12. Source-drain diode forward characteristics



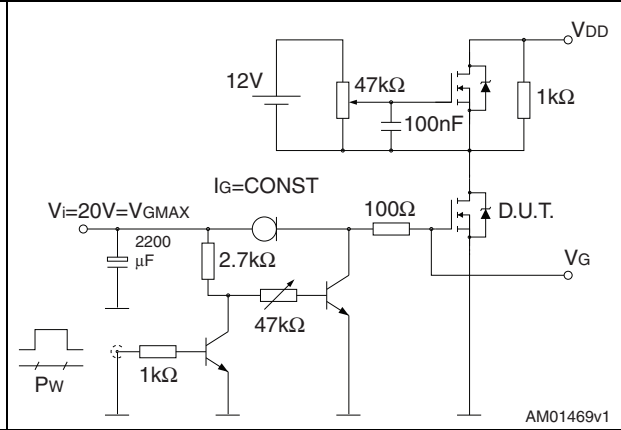
3 Test circuits

Figure 13. Switching times test circuit for resistive load



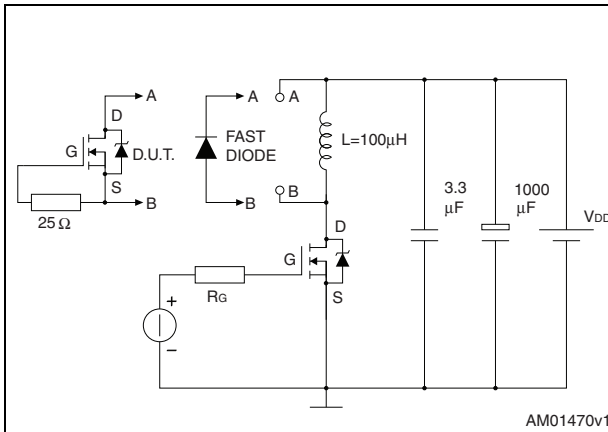
AM01468v1

Figure 14. Gate charge test circuit



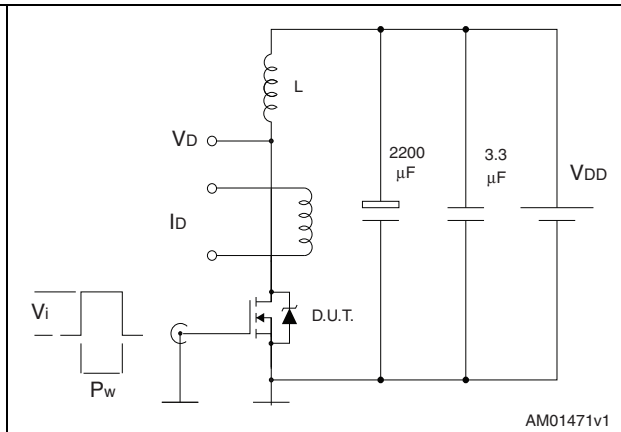
AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



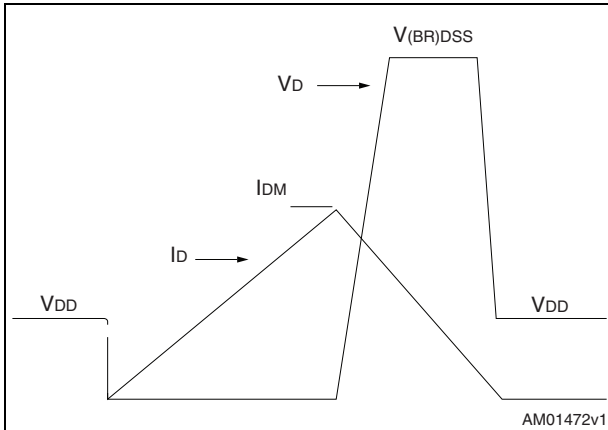
AM01470v1

Figure 16. Unclamped inductive load test circuit



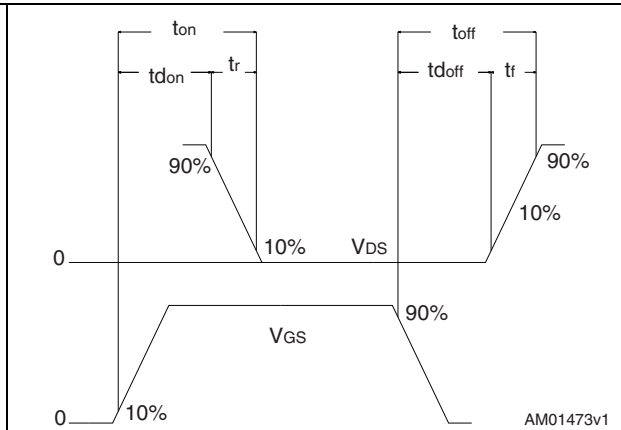
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

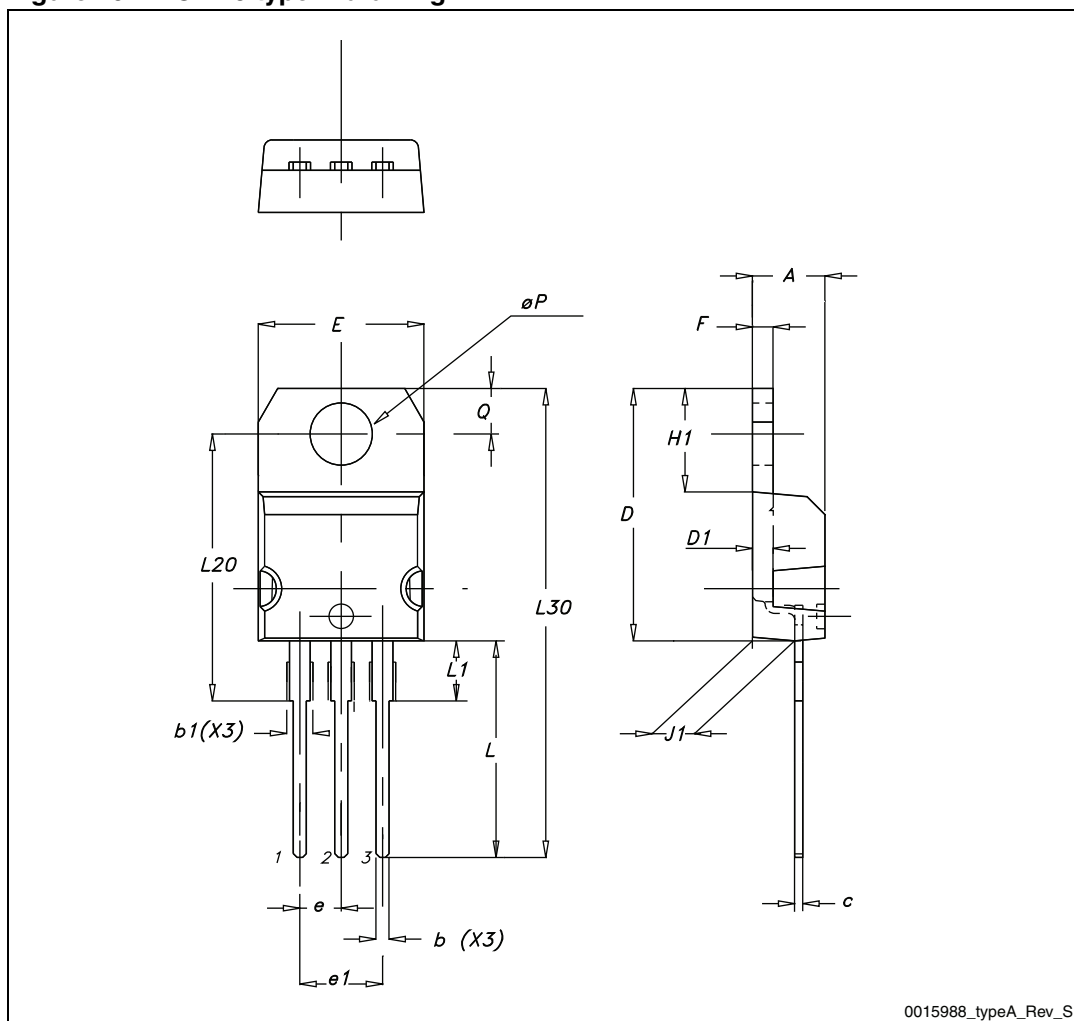
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
06-Dec-2012	1	First release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

